

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

1. **(currently amended)** A method of selective etching comprising:

providing a first material selected from a group A on a substrate;

providing a second material selected from a group B on the substrate;

selectively etching said first material with a selectivity of at least 2:1 towards said second material by dispensing a liquid etchant ~~flowing across onto~~ the substrate surface ~~at a flow sufficiently fast to generate and generating a flow having a~~ mean velocity v parallel to the surface of the substrate of at least 0.1 m/s,

wherein said liquid etchant is dispensed in a continuous flow as a free beam or as a liquid stream onto the substrate and spreads over the surface of the substrate.

2. **(cancelled)**

3. (currently amended) The method of claim 21, wherein the point of impact of ~~a stream of~~ said liquid etchant stream is moved across the surface of the substrate in a time sequence.

4. (currently amended) The method of claim 21, wherein said liquid etchant is dispensed at a volume flow of at least 0.05 l/min.

5. (previously presented) The method of claim 1, wherein said substrate is rotated while exposed to said liquid etchant.

6. (previously presented) The method of claim 1, wherein group A comprises materials with a high dielectric constant.

7. (previously presented) The method of claim 1, wherein group B comprises silicon dioxide and silicon.

8. (previously presented) The method of claim 1, wherein the second material is silicon dioxide and the liquid etchant comprises fluoride ions.

9. (previously presented) The method of claim 1, wherein said first material is pretreated to damage the structure of said first material.

10. (previously presented) The method of claim 9, wherein said pretreatment is performed using an energetic particle bombardment.

11. (previously presented) The method of claim 1, wherein said liquid etchant is selected from the group consisting of:
a solution comprising fluoride ions and an additive for lowering dielectric constant of said solution,
an acidic aqueous solution comprising fluoride ions; and
an acidic aqueous solution comprising fluoride ions and an additive for lowering dielectric number.

12. (previously presented) The method of claim 11, wherein said liquid etchant comprises an analytical concentration of less than 0.01 mol/l of fluoride ions, wherein said analytical concentration is calculated as F^- .

13. (previously presented) The method of claim 1, wherein said liquid etchant comprises fluoride ions and has a pH less than 3.

14. (previously presented) The method of claim 2, wherein the liquid etchant is dispensed at a volume flow of at least 0.5 l/min.

15. (previously presented) The method of claim 11, wherein the additive for lowering dielectric number, in the acidic aqueous solution comprising fluoride ions, is an alcohol.

16. (currently amended) A method of selective etching comprising selectively etching a first material on a substrate with a selectivity of at least 2:1 towards a second material on the substrate, by dispensing a liquid etchant ~~flowing across onto~~ the substrate surface ~~at a flow sufficiently fast to generate and~~ generating a flow having a mean velocity v parallel to the surface of the substrate of at least 0.1 m/s,

wherein said liquid etchant is dispensed in a continuous flow as a free beam or as a liquid stream onto the substrate and spreads over the surface of the substrate.

17. (currently amended) A method of selective etching comprising:

providing a first material on a substrate, wherein said first material is HfO_2 or ZrO_2 , and said first material is pretreated with an energetic particle bombardment;

providing a second material on the substrate; and selectively etching said first material with a selectivity of at least 2:1 towards said second material by dispensing a liquid etchant ~~flowing across onto~~ the substrate surface ~~at a flow sufficiently fast to generate and~~ generating a flow having a

mean velocity v parallel to the surface of the substrate of at least 0.1 m/s,

wherein said liquid etchant is dispensed in a continuous flow as a free beam or as a liquid stream onto the substrate and spreads over the surface of the substrate.